DATA SHEET

HSTL16918
9-bit to 18-bit HSTL-to-LVTTL memory address latch

Product data 2001 Jun 16





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HSTL16918

FEATURES

- Inputs meet JEDEC HSTL Std. JESD 8–6, and outputs meet Level III specifications
- ESD classification testing is done to JEDEC Standard JESD22.
 Protection exceeds 2000 V to HBM per method A114.
- Latch-up testing is done to JEDEC Standard JESD78, which exceeds 100 mA.
- Packaged in 48-pin plastic thin shrink small outline package (TSSOP48)

DESCRIPTION

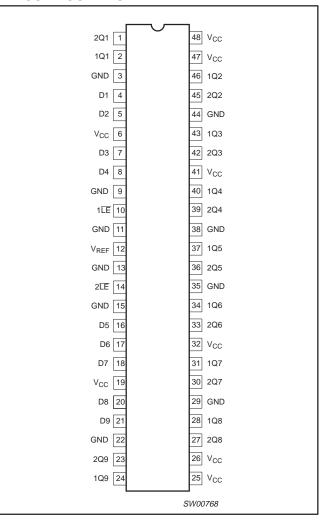
The HSTL16918 is a 9-bit to 18-bit D-type latch designed for 3.15 to 3.45 V V_{CC} operation. The D inputs accept HSTL levels and the Q outputs provide LVTTL levels.

The HSTL16918 is particularly suitable for driving an address bus to two banks of memory. Each bank of nine outputs is controlled with its own latch-enable ($\overline{\text{LE}}$) input.

Each of the nine D inputs is tied to the inputs of two D-type latches that provide true data (Q) at the outputs. While $\overline{\text{LE}}$ is LOW the Q outputs of the corresponding nine latches follow the D inputs. When $\overline{\text{LE}}$ is taken HIGH, the Q outputs are latched at the levels set up at the D inputs.

The HSTL16918 is characterized for operation from 0 to +70 $^{\circ}$ C.

PIN CONFIGURATION



ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE	DWG NUMBER
48-pin plastic thin shrink small outline package (TSSOP48)	0 to +70 °C	HSTL16918DGG	SOT362-1

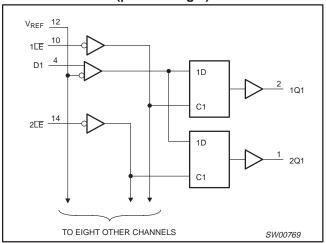
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PIN DESCRIPTION

PIN	SYMBOL	FUNCTION
4, 5, 7, 8, 16, 17, 18, 20, 21	D[1-9]	Inputs
2, 46, 43, 40, 37, 34, 31, 28, 24	1Q[1–9]	Outouto
1, 45, 42, 39, 36, 33, 30, 27, 23	2Q[1-9]	Outputs
10	1LE	Latch enable
14	2LE	Laterrable
12	V_{REF}	Reference voltage
6, 19, 25, 26, 32, 41, 47, 48	V _{CC}	Supply voltage
3, 9, 11, 13, 15, 22, 29, 35, 38, 44	GND	Ground

LOGIC DIAGRAM (positive logic)



FUNCTION TABLE

INP	OUTPUT	
LE	D	Q
L	Н	Н
L	L	L
Н	X	Q ₀ 1

NOTE:
1. Output level before the indicated steady-state input conditions were established.

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ABSOLUTE MAXIMUM RATINGS¹

Over operating free-air temperature range (unless otherwise noted).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	Supply voltage range		-0.5 to +4.6	V
VI	Input voltage range ²		-0.5 to V _{CC} +0.5	V
V _O	Output voltage range ²		-0.5 to V _{CC} +0.5	V
I _{IK}	Input clamp current	V _I < 0	– 50	mA
I _{OK}	Output clamp current ³	$V_O < 0$ or $V_O > V_{CC}$	±50	mA
I _O	Continuous output current	$V_O = 0$ to V_{CC}	±50	mA
	Continuous current through each V _{CC} or GND		±100	mA
$\theta_{\sf JA}$	Package thermal impedance ⁴		89	°C/W
T _{stg}	Storage temperature range		-65 to +150	°C

NOTES:

- 1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 This current flows only when the output is in the high state and V_O > V_{CC}.
 The package thermal impedance is calculated in accordance with JESD 51.

RECOMMENDED OPERATING CONDITIONS¹

OVMDOL	DADAMETED		LINUT			
SYMBOL	PARAMETER	Min	Nom	Max	UNIT	
V _{CC}	Supply voltage		3.15		3.45	V
V_{REF}	Reference voltage		0.68	0.75	0.9	V
V_{I}	Input voltage		0		1.5	V
V_{IH}	AC high-level input voltage	All inputs	V _{REF} + 200 mV			V
V_{IL}	AC low-level input voltage	All inputs			V _{REF} – 200 mV	V
V_{IH}	DC high-level input voltage	All inputs	V _{REF} + 100 mV			V
V_{IL}	DC low-level input voltage	All inputs			V _{REF} – 100 mV	V
l _{OH}	High-level output current				-24	mA
I _{OL}	Low-level output current			24	mA	
T _{amb}	Operating free-air temperature range		0		+70	°C

NOTE:

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^{1.} All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

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ELECTRICAL CHARACTERISTICS

Over recommended operating free-air temperature range (unless otherwise noted).

OVMDOL	DADAMETED	TEGT COMPITIONS		LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS	Min	Typ ¹	Max	UNIT
V _{IK}		$V_{CC} = 3.15 \text{ V; } I_{I} = -18 \text{ mA}$			-1.2	V
V _{OH}		$V_{CC} = 3.15 \text{ V; } I_{OH} = -24 \text{ mA}$	2.4			V
V _{OL}		$V_{CC} = 3.15 \text{ V}; I_{OL} = 24 \text{ mA}$			0.5	V
	Control inputs	$V_{CC} = 3.45 \text{ V}; V_{I} = 0 \text{ or } 1.5 \text{ V}$			±5	μΑ
l _l	Data inputs	$V_{CC} = 3.45 \text{ V}; V_{I} = 0 \text{ or } 1.5 \text{ V}$			±5	μΑ
	V _{REF}	V _{CC} = 3.45 V; V _{REF} = 0.68 V or 0.9 V			90	μΑ
I _{CC}		$V_{CC} = 3.45 \text{ V}; V_{I} = 0 \text{ or } 1.5 \text{ V}$		50	100	mA
	Control inputs	V _{CC} = 0 or 3.3 V; V _I = 0 or 3.3 V		2		pF
Cl	Data inputs	V _{CC} = 0 or 3.3 V; V _I = 0 or 3.3 V		2.5		pF
Co	Outputs	V _{CC} = 0 V; V _O = 0 V		4		pF

NOTE:

TIMING REQUIREMENTS

Over recommended operating free-air temperature range (unless otherwise noted).

SYMBOL	PARAMETER	TEST CONDITIONS	$V_{CC} = 3.3$	UNIT		
STWIBOL	PARAMETER	TEST CONDITIONS	Min	Max	Olan	
t _w	Pulse duration	LE LOW (Figure 1)	3		ns	
t _{su}	Setup time	D before LE ↑ (Figure 2)	2		ns	
t _h	Hold time	D after LE ↑ (Figure 2)	1		ns	
t _{ldr}	Data race condition time ¹	D after LE ↓		0	ns	

NOTE:

SWITCHING CHARACTERISTICS

Over recommended operating free-air temperature range; $V_{REF} = 0.75 \text{ V}$.

SYMBOL	PARAMETER	FROM	то	V _{CC} = 3.3	UNIT		
STWIBOL	PARAMETER	(INPUT)	(OUTPUT)	Min	Max	UNIT	
	Dropogation delay (Figure 2)	D	Q	1.9	3.4	ns	
^L pd	t _{pd} Propagation delay (Figure 3)		Q	1.9	4.2	ns	

SIMULTANEOUS SWITCHING CHARACTERISTICS

Over recommended operating free-air temperature range; V_{REF} = 0.75 V

SYMBOL	PARAMETER	FROM	то	V _{CC} = 3.3	UNIT	
STWIBOL	PARAMETER	(INPUT)	(OUTPUT)	Min	Max	ONIT
	Propagation delay; all outputs switching	D	Q	1.9	4.4	ns
t _{pd}	(Figure 3)	LE	Q	1.9	5.2	ns

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^{1.} All typical values are at V_{CC} = 3.3 V; T_{amb} = 25 °C.

^{1.} This is the maximum time after E switches LOW that the data input can return to the latched state from the opposite state without producing a glitch on the output.

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VOLTAGE WAVEFORMS

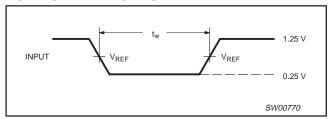


Figure 1. Pulse duration

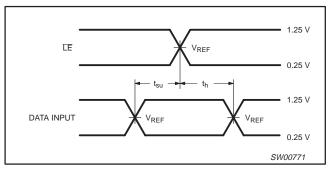


Figure 2. Setup and Hold times

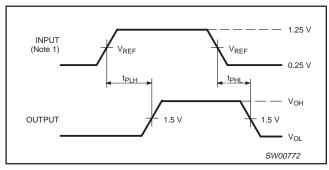
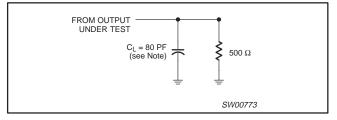


Figure 3. Propagation delay times

NOTES:

- 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O=50~\Omega,~t_r\leq 1~ns,~t_f\leq 1~ns.$
- 2. The outputs are measured one at a time with one transition per measurement.
- 3. t_{PHL} and t_{PLH} are the same as t_{pd} .

LOAD CIRCUIT



NOTE: C_L includes probe and jig capacitance.

Figure 4. Load circuit

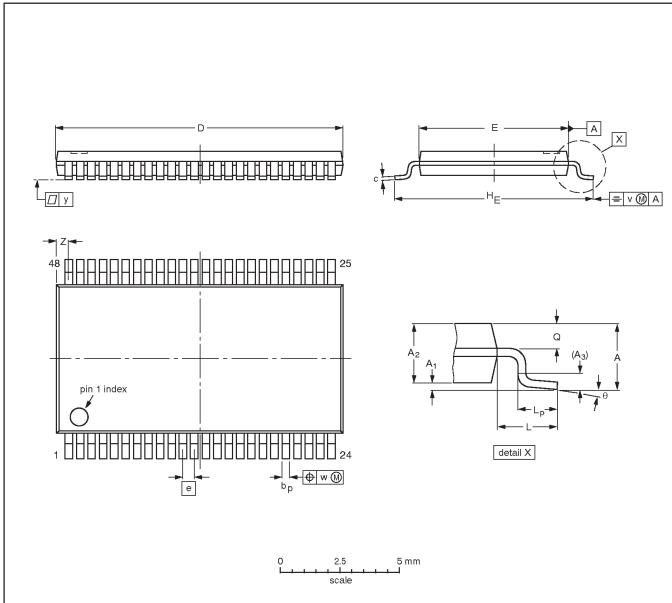
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TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



DIMENSIONS (mm are the original dimensions).

UNIT	A max.	Α1	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	٧	w	у	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES		EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
SOT362-1		MO-153				-95-02-10- 99-12-27	

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Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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